

# PBSS4350X,135 Datasheet



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DiGi Electronics Part Number PBSS4350X,135-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PBSS4350X,135

Description TRANS NPN 50V 3A SOT89

**Detailed Description** Bipolar (BJT) Transistor NPN 50 V 3 A 100MHz 1.6 W

Surface Mount SOT-89



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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
PBSS4350X,135	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN	3 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
50 V	370mV @ 300mA, 3A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA	300 @ 1A, 2V
Power - Max:	Frequency - Transition:
1.6 W	100MHz
Operating Temperature:	Grade:
150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q100	Surface Mount
Package / Case:	Supplier Device Package:
TO-243AA	SOT-89
Base Product Number:	
PBSS4350	

# **Environmental & Export classification**

8541.29.0075

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



**Product data sheet** 

# 1. General description

NPN low V<sub>CEsat</sub> transistor in a SOT89 plastic package.

PNP complement: PBSS5350X

#### 2. Features and benefits

- SOT89 (SC-62) package
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability: I<sub>C</sub> and I<sub>CM</sub>
- · Higher efficiency leading to less heat generation
- · Reduced printed-circuit board requirements
- AEC-Q101 qualified

### 3. Applications

- Power management
  - · DC/DC converters
  - Supply line switching
  - Battery charger
  - LCD backlighting
- Peripheral drivers
  - Driver in low supply voltage applications (e.g. lamps and LEDs)
  - Inductive load driver (e.g. relays, buzzers and motors)

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	-	50	V
I <sub>C</sub>	collector current		-	-	3	Α
I <sub>CM</sub>	peak collector current	limited by T <sub>j(max)</sub>	-	-	5	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 2 A; $I_B$ = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	100	130	mΩ



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		
3	В	base		B — [
			3 2 1	E
			SOT89	sym123

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PBSS4350X		plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89			

### 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBSS4350X	S43

# 8. Limiting values

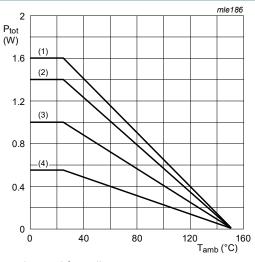
#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	50	V
$V_{CEO}$	collector-emitter voltage	open base		-	50	V
$V_{EBO}$	emitter-base voltage	open collector		-	5	V
I <sub>C</sub>	collector current			-	3	А
I <sub>CM</sub>	peak collector current	limited by T <sub>j(max)</sub>		-	5	А
I <sub>B</sub>	base current			-	0.5	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	550	mW
			[2]	-	1	W
			[3]	-	1.4	W
			[4]	-	1.6	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB 7 cm<sup>2</sup>, single-sided copper, tin-plated.

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- (1) Ceramic PCB; 7 cm<sup>2</sup> mounting pad for collector (2) FR4 PCB; 6 cm<sup>2</sup> copper mounting pad for collector (3) FR4 PCB; 1 cm<sup>2</sup> copper mounting pad for collector

- (4) Standard footprint

**Power derating curves** Fig. 1.

#### 9. Thermal characteristics

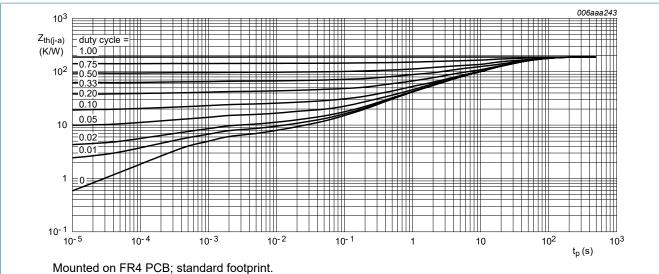
**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	from in free air [	[1]	-	-	225	K/W	
	junction to ambient [2	[2]	-	-	125	K/W	
		[3]	-	-	90	K/W	
		[4]	-	-	80	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. [3]
- Device mounted on a ceramic PCB 7 cm<sup>2</sup>, single-sided copper, tin-plated.

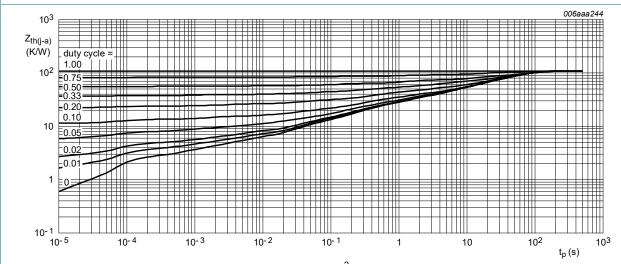
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#### 50 V, 3 A NPN low VCEsat transistor



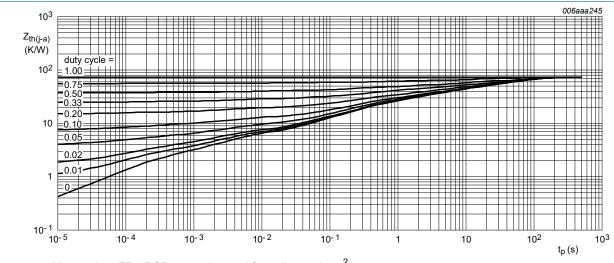
Mounted on FR4 FCB, Standard Tootprint.

Fig. 2. Transient thermal impedance as a function of pulse duration; typical values



Mounted on FR4 PCB; mounting pad for collector 1 cm<sup>2</sup>

Fig. 3. Transient thermal impedance as a function of pulse duration; typical values



Mounted on FR4 PCB; mounting pad for collector 6 cm<sup>2</sup>

Fig. 4. Transient thermal impedance as a function of pulse duration; typical values

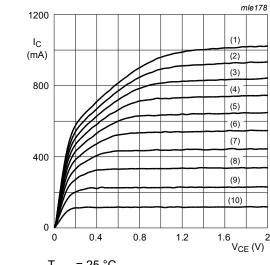
50 V, 3 A NPN low VCEsat transistor

# 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = 10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	50	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage (collector open)	$I_E = 100 \mu A; I_C = 0 A; T_{amb} = 25 °C$	5	-	-	V
Сво	collector-base cut-off	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	50	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = 50 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
I <sub>ЕВО</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 2 V; $I_{C}$ = 0.1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 2; $T_{amb}$ = 25 °C	300	-	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 0.5 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	300	-	-	
	$V_{CE}$ = 2 V; $I_{C}$ = 1 A; pulsed; $t_{p} \le 300 \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	300	-	700		
	$V_{CE}$ = 2 V; $I_{C}$ = 2 A; pulsed; $t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	200	-	-		
		$V_{CE}$ = 2 V; $I_{C}$ = 3 A; pulsed; $t_{p} \le 300 \ \mu s$ ; δ ≤ 0.02; $T_{amb}$ = 25 °C	100	-	-	
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = 0.5 A; I <sub>B</sub> = 50 mA; T <sub>amb</sub> = 25 °C	-	-	80	mV
	saturation voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 50 mA; T <sub>amb</sub> = 25 °C	-	-	160	mV
		$I_C$ = 2 A; $I_B$ = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	280	mV
		$I_C$ = 2 A; $I_B$ = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	260	mV
		$I_C$ = 3 A; $I_B$ = 300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	370	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 2 A; $I_B$ = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	100	130	mΩ
V <sub>BEsat</sub>	base-emitter saturation	I <sub>C</sub> = 2 A; I <sub>B</sub> = 100 mA; T <sub>amb</sub> = 25 °C	-	-	1.1	V
	voltage	$I_C$ = 3 A; $I_B$ = 300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	1.2	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = 2 \text{ V; } I_{C} = 1 \text{ A; } T_{amb} = 25 \text{ °C}$	-	-	1.1	V
fт	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C	-	-	25	pF

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 $T_{amb}$  = 25 °C

(1)  $I_B = 2600 \mu A$ 

(2)  $I_B = 2340 \mu A$ 

 $(3) I_B = 2080 \mu A$ 

 $(4) I_B = 1820 \mu A$ 

 $(5) I_B = 1560 \mu A$ 

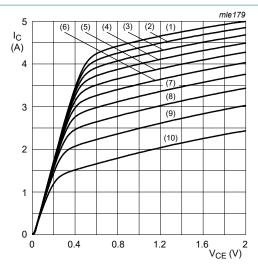
(6)  $I_B = 1300 \mu A$ 

 $(7) I_B = 1040 \mu A$ (8)  $I_B = 780 \, \mu A$ 

(9)  $I_B = 520 \mu A$ 

 $(10) I_B = 260 \mu A$ 

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 $T_{amb}$  = 25 °C

(1)  $I_B = 120 \text{ mA}$ 

(2) I<sub>B</sub> = 108 mA (3) I<sub>B</sub> = 96 mA

 $(4) I_B = 84 \text{ mA}$ 

 $(5) I_{B} = 72 \text{ mA}$ 

(6)  $I_B = 60 \text{ mA}$ 

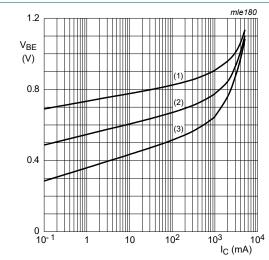
 $(7) I_B = 48 \text{ mA}$ 

(8)  $I_B = 36 \text{ mA}$ 

(9)  $I_B = 24 \text{ mA}$ 

 $(10) I_B = 12 mA$ 

Fig. 6. Collector current as a function of collectoremitter voltage; typical values

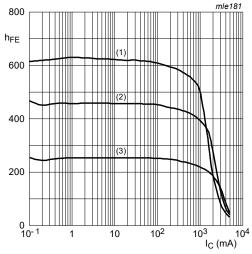


 $V_{CE} = 2 V$ 

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

Fig. 7. Base-emitter voltage as a function of collector current; typical values



 $V_{CE} = 2 V$ (1)  $T_{amb} = 100 °C$ 

(2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -55 °C

Fig. 8. DC current gain as a function of collector current; typical values

#### 50 V, 3 A NPN low VCEsat transistor

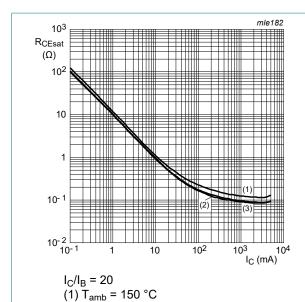


Fig. 9. Equivalent on-resistance as a function of collector current; typical values

(2) T<sub>amb</sub> = 25 °C

 $(3) T_{amb} = -55 °C$ 

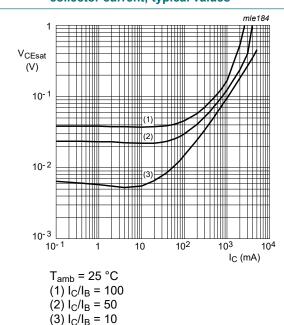


Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values

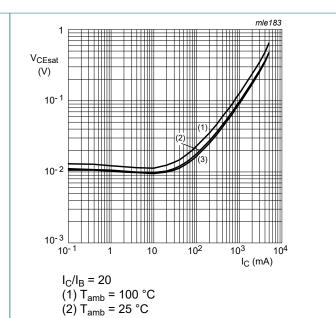


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

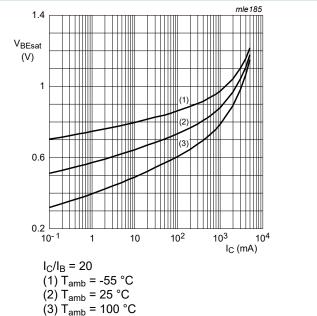


Fig. 12. Base-emitter saturation voltage as a function of collector current; typical values

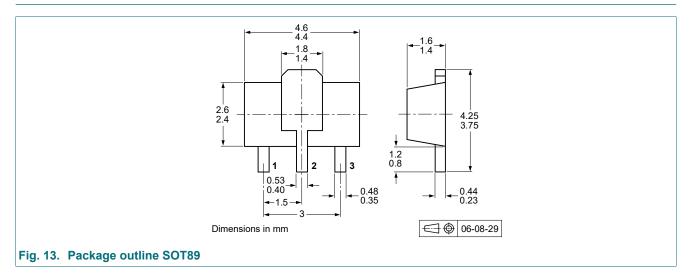
#### 11. Test information

#### **Quality information**

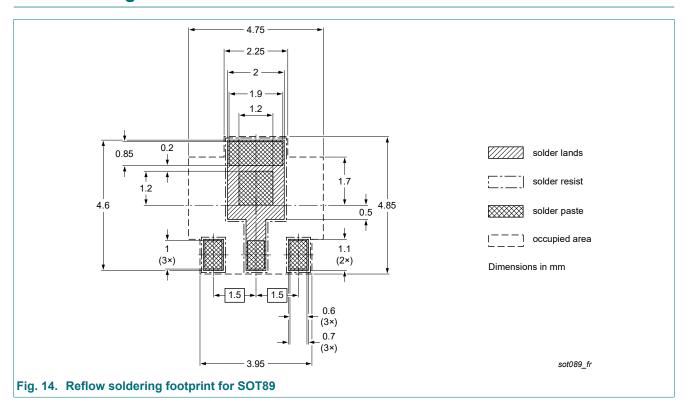
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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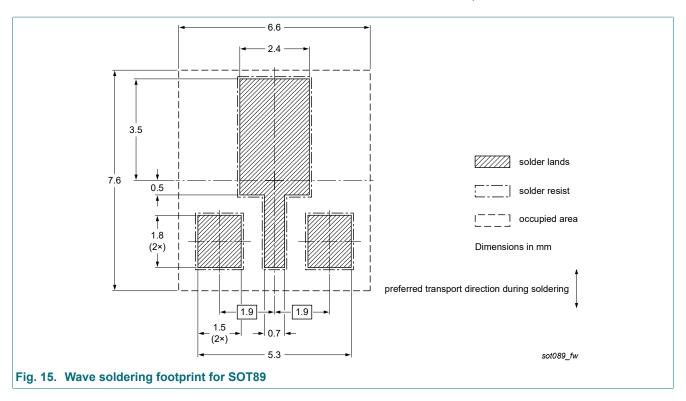
# 12. Package outline



# 13. Soldering



#### 50 V, 3 A NPN low VCEsat transistor



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# 14. Revision history

#### Table 8. Revision history

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Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS4350X v.3	20220516	Product data sheet	-	PBSS4350X v.2			
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>						
PBSS4350X v.2	20041104	Product data sheet	-	PBSS4350X v.1			
PBSS4350X v.1	20031121	Product data sheet	-	-			

#### 50 V, 3 A NPN low VCEsat transistor

### 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 16 May 2022

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